

Technical Data Sheet Opto Interrupter

ST966

Features

- Fast response time
- High analytic
- Cut-off visible wavelength λp=940nm
- High sensitivity
- Pb free
- The product itself will remain within RoHS compliant version.

Descriptions

The **ST966** consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black Thermoplastic
Housing The phototransistor receives radiation from the IRED only .This is the normal Situation. But when an object is in between , phototransistor could not receives the radiation. For additional component information , please refer to IR928-6C and PT928-6C

Applications

- Mouse Copier
- Switch Scanner
- Floppy disk driver
- Non-contact Switching
- For Direct Board

Device Selection Guide

Device No.	Chip Material	LENS COLOR	
IR928C	GaAlAs	Waterclear	
PT928C	Silicon	Waterclear	

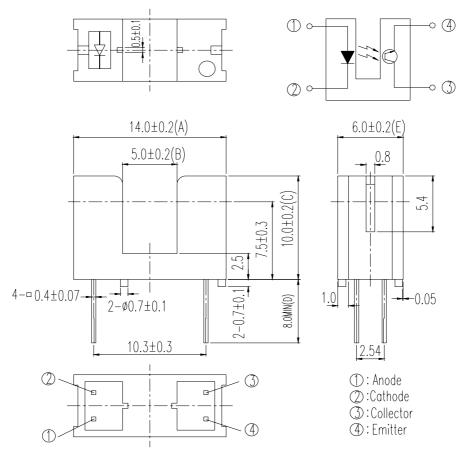


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Package Dimensions



Notes:

- 1.All dimensions are in millimeters
- 2. Tolerances unless dimensions ±0.2mm
- 3. Lead spacing is measured where the lead emerge from the package

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Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	100	mW
	Reverse Voltage	V_R	5	V
	Forward Current	I_{F}	50	mA
	Peak Forward Current (*1) Pulse width $\leq 100 \mu$ s, Duty cycle=1%	$ m I_{FP}$	1	A
Output	Collector Power Dissipation	P_{C}	75	mW
	Collector Current	I_{C}	50	mA
	Collector-Emitter Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{CEO}}$	30	V
	Emitter-Collector Voltage	$\mathrm{B}\mathrm{V}_{\mathrm{ECO}}$	5	V
Operating Temperature		Topr	-25~+85	$^{\circ}\!\mathbb{C}$
Storage Temperature		Tstg	-40~+85	$^{\circ}$ C
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	$^{\circ}\mathbb{C}$

(*1) tw=100 μ sec., T=10 msec. (*2) t=5 Sec

Electro-Optical Characteristics (Ta=25°C)

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Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input		$ m V_{F1}$		1.2	1.6	V	$I_F=20\text{mA}$	
	Forward Voltage	$ m V_{F2}$		1.4	1.85		I_F =100mA,tp=100 μ s,tp/T=0.01	
		$ m V_{F3}$		2.6	4.0		I_F =1A,tp=100 μ s,tp/T=0.01	
	Reverse Current	I_R			10	μ A	V _R =5V	
	Peak Wavelength	λ_P		940		nm	$I_F=20\text{mA}$	
	View Angle	201/2		60		Deg	$I_F=20\text{mA}$	
Output	Dark Current	I_{CEO}		-	100	nA	$V_{CE}=20V, Ee=0mW/cm^2$	
	C-E Saturation Voltage	V _{CE} (sat)			0.4	V	$I_{C}=2mA$, $Ee=1mW/cm^{2}$	
Transfer Characteristics	Collect Current	I _C (ON)	0.5		10	mA	V_{CE} =5 V I_F =20 mA	
	Rise time	$t_{\rm r}$		15		$\mu \sec$	V _{CE} =5V	
		${ m t_f}$		15		μ sec	$I_{C}=1 \text{mA}$	
		ι _Ī					$R_L=1K\Omega$	

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